



**THE DATASHEET OF  
ZVP4105ASTOA**



## P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

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### FEATURES

- \* 50 Volt  $V_{DS}$
- \*  $R_{DS(on)} = 10\Omega$
- \* Low threshold

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL
Drain-Source Voltage	$V_{DS}$
Continuous Drain Current at $T_{amb}=25^{\circ}\text{C}$	$I_{D}$
Pulsed Drain Current	$I_{D(p)}$
Gate Source Voltage	$V_{GS}$
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$P_{D}$
Operating and Storage Temperature Range	$T_{stg}$

### ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	$BV_{DSS}$
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	$I_{GSS}$
Zero Gate Voltage Drain Current	$I_{DSS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	$g_{fs}$
Input Capacitance (2)(4)	$C_{iss}$
Common Source Output Capacitance (2)(4)	$C_{oss}$
Reverse Transfer Capacitance (2)(4)	$C_{riss}$
Turn-On Delay Time (2)(3)(4)	$t_{d(on)}$
Rise Time (2)(3)(4)	$t_r$
Turn-Off Delay Time (2)(3)(4)	$t_{d(off)}$
Fall Time (2)(3)(4)	$t_f$

(1) Measured under pulsed conditions.  $V_{GS} = 10\text{V}$ ,  $V_{DS} = 10\text{V}$ ,  $I_D = 10\text{mA}$ .



(2) Sample test.

(3) Switching times measured with  $50\Omega$  source and load.

NOT RECOMMENDED ↴

## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View ZVP4105ASTOA on WIN SOURCE](#)
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